



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-220 Plastic-Encapsulate Transistors

2SB834 TRANSISTOR (PNP)

FEATURES

Power dissipation

P_{CM} : 1.5 W ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : -3 A

Collector-base voltage

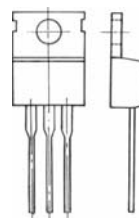
$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

TO-220

1. BASE
2. COLLECTOR
3. EMITTER



1 2 3

ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=-100\mu A, I_E=0$	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=-50mA, I_B=0$	-60			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=-100\mu A, I_C=0$	-7			V
Collector cut-off current	I_{CBO}	$V_{CB}=-60V, I_E=0$			-100	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=-7V, I_C=0$			-100	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=-5V, I_C=-500mA$	60		200	
	$h_{FE(2)}$	$V_{CE}=-5V, I_C=-3A$	20			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=-3A, I_B=-0.3A$			-1	V
Base-emitter voltage	V_{BE}	$V_{CE}=-5V, I_C=-500mA$			-1	V
Transition frequency	f_T	$V_{CE}=-5V, I_C=-500mA$		9		MHz
Collector output capacitance	C_{ob}	$V_{CB}=-10V, I_E=0, f=1MHz$		150		pF
Turn-on Time	t_{on}	$V_{CC}=-30V, I_C=-2A,$ $I_{B1}=I_{B2}=-0.2A$		0.4		μs
Storage Time	t_{stg}			1.7		μs
Turn-off Time	t_{off}			0.5		μs

CLASSIFICATION OF $h_{FE(1)}$

Rank	O	Y
Range	60-120	100-200